

DESCRIPTION/产品描述

epoxy bare sealed, silicon photodiode, moderate size, wide receiving angle, small dark current, fast response and wide application.

环氧裸封，硅光电二极管，尺寸小，接收角度大，暗电流较小，响应速度快，应用广泛。

APPLICATIONS/典型应用

- photo detector/光电探测
- Security system /安防
- Camera/相机

FEATURES/特性

- Fast response time/反应快
- High photo sensitivity/灵敏度高

TYPICAL ABSOLUTE MAXIMUM RATINGS/ 典型额定参数

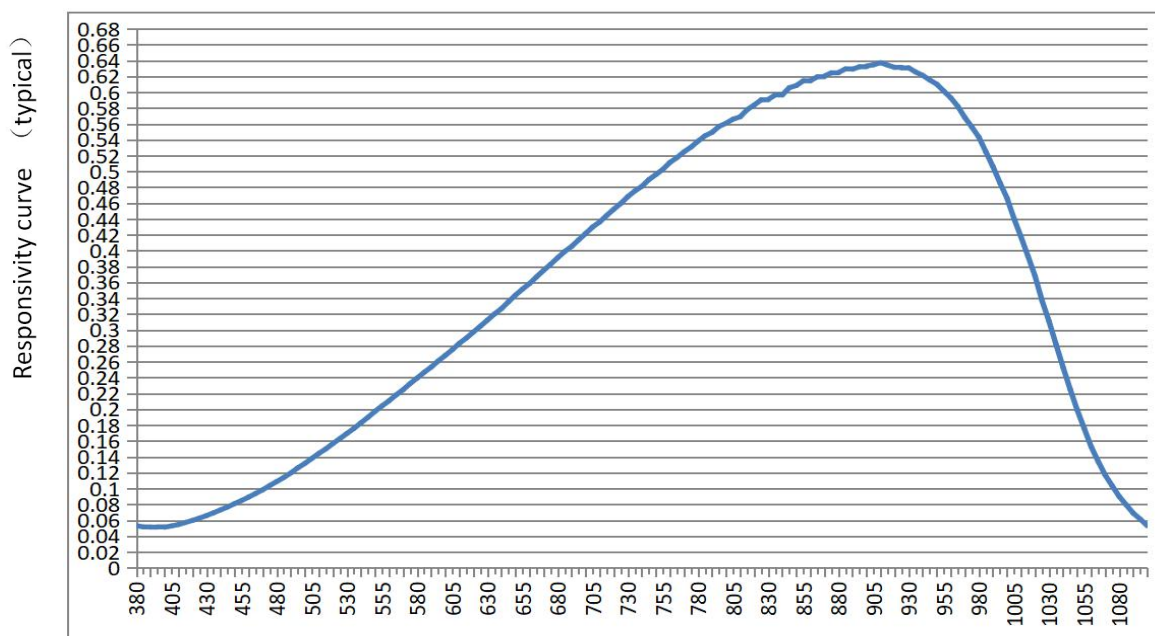
SYMBOL/符号		UNITS/单位	
BVR/反向击穿电压	20	V	Reverse Breakdown Voltage @25°C
Storage Temperature/贮存温度	-20 to +75	°C	-
Operating Temperature/工作温度	-20 to +65	°C	-
Soldering Temperature*/焊接温度	+260	°C	*Soldering Time < 3s/焊接时间小于 3s

* 1/8 inch(>3mm) from case for 3 seconds max.

TYPICAL OPTO-ELECTRICAL PARAMETERS@25°C/典型光电参数

PARAMETER 项目	TEST CONDITIONS 测试条件	MIN 下限	TPY 典型	MAX 上限	UNITS 单位
Forward Voltage 正向电压	$I_F = 10 \text{ mA}$	0.5		1.3	V
Light Current (2856K) 亮电流	$V_R = 5V; E_v = 1000 \text{ lux}$		36.5		μA
Dark Current 暗电流	$V_R = 5V; E_v = 0 \text{ Lux}$	10			nA
Spectrum Sensitivity 光谱响应范围		430		1100	nm
Peak Sensing Wavelength 峰值波长			940		nm

TYPICAL PERFORMANCE/典型曲线



Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.